

### General Description

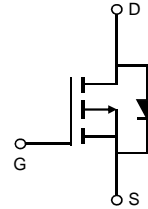
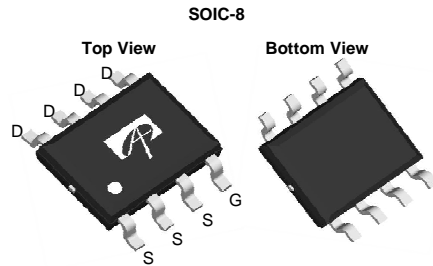
The AO4407 combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

\* RoHS and Halogen-Free Compliant

### Product Summary

|                                  |                |
|----------------------------------|----------------|
| $V_{DS}$                         | -30V           |
| $I_D$ (at $V_{GS}=-20V$ )        | -12A           |
| $R_{DS(ON)}$ (at $V_{GS}=-20V$ ) | < 13m $\Omega$ |
| $R_{DS(ON)}$ (at $V_{GS}=-10V$ ) | < 14m $\Omega$ |
| $R_{DS(ON)}$ (at $V_{GS}=-5V$ )  | < 30m $\Omega$ |

100% UIS Tested  
 100%  $R_g$  Tested



### Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

| Parameter                               | Symbol           | Maximum          | Units      |
|---|------------------|------------------|------------|
| Drain-Source Voltage                    | $V_{DS}$         | -30              | V          |
| Gate-Source Voltage                     | $V_{GS}$         | $\pm 25$         | V          |
| Continuous Drain Current                | $I_D$            | $T_A=25^\circ C$ | -12        |
|   |                  | $T_A=70^\circ C$ | -10        |
| Pulsed Drain Current <sup>C</sup>       | $I_{DM}$         | -60              | A          |
| Avalanche Current <sup>C</sup>          | $I_{AS}, I_{AR}$ | 26               | A          |
| Avalanche energy $L=0.3mH$ <sup>C</sup> | $E_{AS}, E_{AR}$ | 101              | mJ         |
| Power Dissipation <sup>B</sup>          | $P_D$            | $T_A=25^\circ C$ | 3.1        |
|   |                  | $T_A=70^\circ C$ | 2          |
| Junction and Storage Temperature Range  | $T_J, T_{STG}$   | -55 to 150       | $^\circ C$ |

### Thermal Characteristics

| Parameter                                  | Symbol          | Typ | Max | Units        |
|--|-----------------|-----|-----|--------------|
| Maximum Junction-to-Ambient <sup>A</sup>   | $R_{\theta JA}$ | 31  | 40  | $^\circ C/W$ |
| Maximum Junction-to-Ambient <sup>A D</sup> |                 | 59  | 75  | $^\circ C/W$ |
| Maximum Junction-to-Lead                   | $R_{\theta JL}$ | 16  | 24  | $^\circ C/W$ |

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

| Symbol                      | Parameter                             | Conditions   | Min  | Typ      | Max      | Units |
|-----------------------------|---------------------------------------|--|------|----------|----------|-------|
| <b>STATIC PARAMETERS</b>    |                                       |  |      |          |          |       |
| BV <sub>DSS</sub>           | Drain-Source Breakdown Voltage        | I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V  | -30  |          |          | V     |
| I <sub>DSS</sub>            | Zero Gate Voltage Drain Current       | V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V<br>T <sub>J</sub> =55°C                           |      |          | -1<br>-5 | μA    |
| I <sub>GSS</sub>            | Gate-Body leakage current             | V <sub>DS</sub> =0V, V <sub>GS</sub> = ±25V  |      |          | ±100     | nA    |
| V <sub>GS(th)</sub>         | Gate Threshold Voltage                | V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA                                      | -1.7 | -2.25    | -2.8     | V     |
| I <sub>D(ON)</sub>          | On state drain current                | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-5V  | -60  |          |          | A     |
| R <sub>DS(ON)</sub>         | Static Drain-Source On-Resistance     | V <sub>GS</sub> =-20V, I <sub>D</sub> =-12A  |      | 8.5      | 13       | mΩ    |
|                             |                                       | V <sub>GS</sub> =-10V, I <sub>D</sub> =-12A<br>T <sub>J</sub> =125°C                         |      | 10<br>12 | 14<br>19 | mΩ    |
|                             |                                       | V <sub>GS</sub> =-5V, I <sub>D</sub> =-7A  |      | 19       | 30       | mΩ    |
| g <sub>FS</sub>             | Forward Transconductance              | V <sub>DS</sub> =-5V, I <sub>D</sub> =-10.5A   |      | 27       |          | S     |
| V <sub>SD</sub>             | Diode Forward Voltage                 | I <sub>S</sub> =-1A, V <sub>GS</sub> =0V   |      | -0.72    | -1       | V     |
| I <sub>S</sub>              | Maximum Body-Diode Continuous Current |  |      |          | -4       | A     |
| <b>DYNAMIC PARAMETERS</b>   |                                       |  |      |          |          |       |
| C <sub>iss</sub>            | Input Capacitance                     | V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz   |      | 2060     | 2600     | pF    |
| C <sub>oss</sub>            | Output Capacitance                    |  |      | 370      |          | pF    |
| C <sub>rss</sub>            | Reverse Transfer Capacitance          |  |      | 295      |          | pF    |
| R <sub>g</sub>              | Gate resistance                       | V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz   | 1.2  | 2.4      | 3.6      | Ω     |
| <b>SWITCHING PARAMETERS</b> |                                       |  |      |          |          |       |
| Q <sub>g</sub>              | Total Gate Charge                     | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-12A                           | 24   | 30       | 36       | nC    |
| Q <sub>gs</sub>             | Gate Source Charge                    |  |      | 4.6      |          | nC    |
| Q <sub>gd</sub>             | Gate Drain Charge                     |  |      | 10       |          | nC    |
| t <sub>D(on)</sub>          | Turn-On DelayTime                     | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V,<br>R <sub>L</sub> =1.25Ω, R <sub>GEN</sub> =3Ω |      | 11       |          | ns    |
| t <sub>r</sub>              | Turn-On Rise Time                     |  |      | 9.4      |          | ns    |
| t <sub>D(off)</sub>         | Turn-Off DelayTime                    |  |      | 24       |          | ns    |
| t <sub>f</sub>              | Turn-Off Fall Time                    |  |      | 12       |          | ns    |
| t <sub>rr</sub>             | Body Diode Reverse Recovery Time      | I <sub>F</sub> =-12A, di/dt=100A/μs  |      | 30       | 40       | ns    |
| Q <sub>rr</sub>             | Body Diode Reverse Recovery Charge    | I <sub>F</sub> =-12A, di/dt=100A/μs  |      | 22       |          | nC    |

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

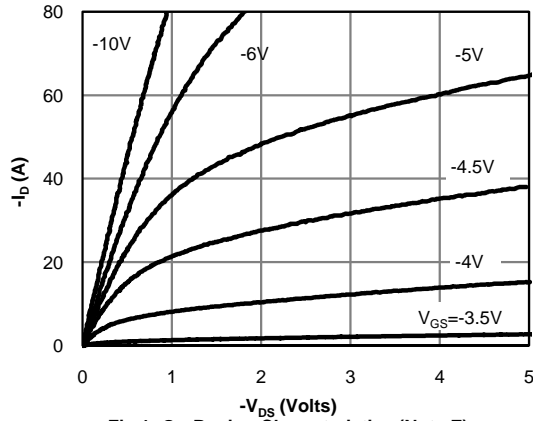
D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

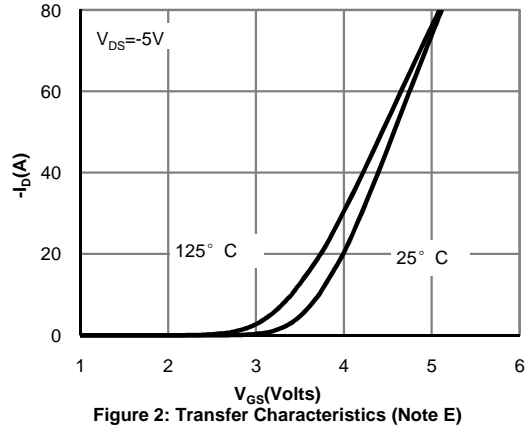
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

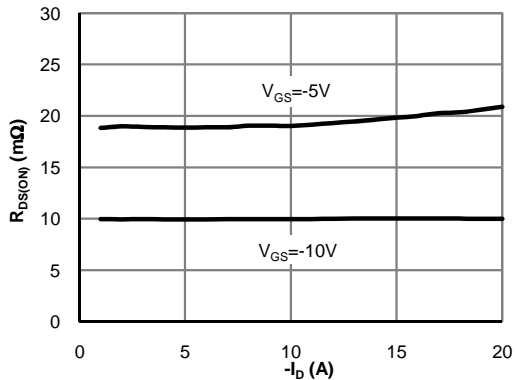
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



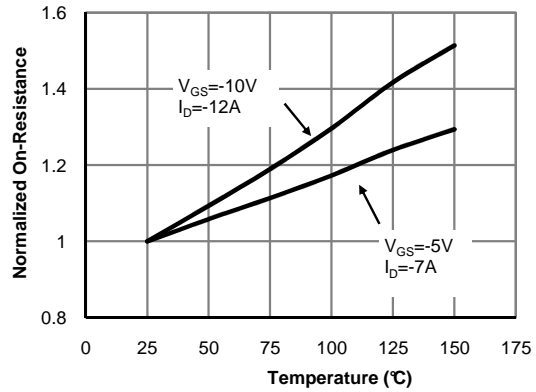
**Figure 1: On-Region Characteristics (Note E)**



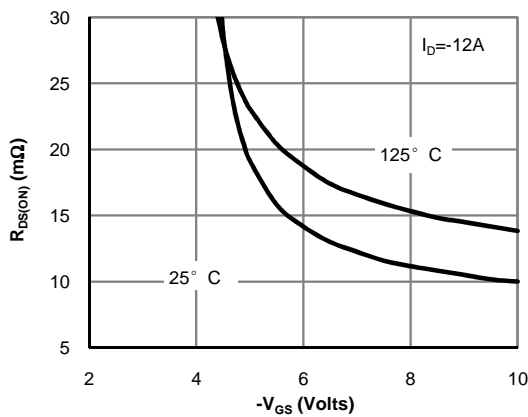
**Figure 2: Transfer Characteristics (Note E)**



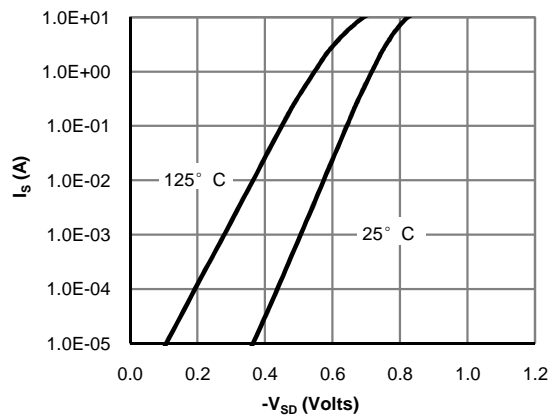
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

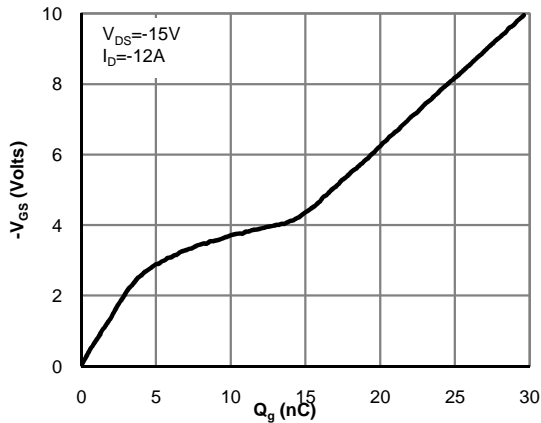


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

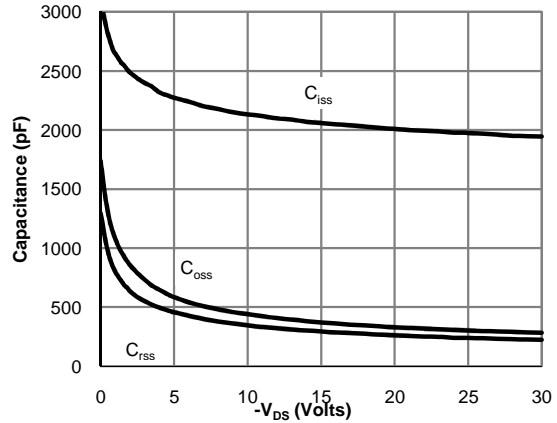


**Figure 6: Body-Diode Characteristics (Note E)**

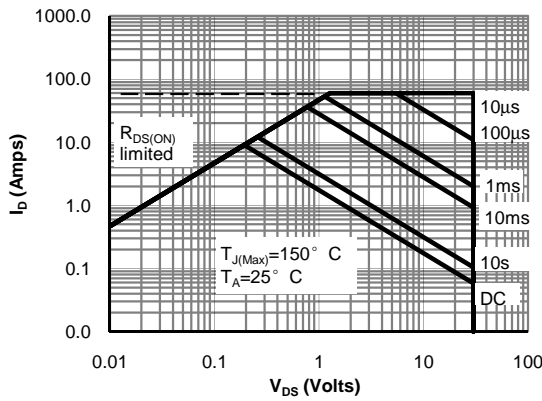
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



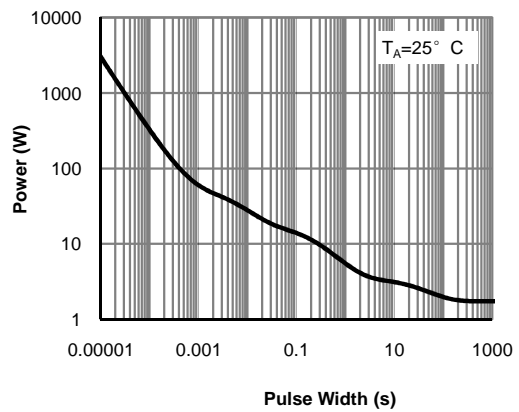
**Figure 7: Gate-Charge Characteristics**



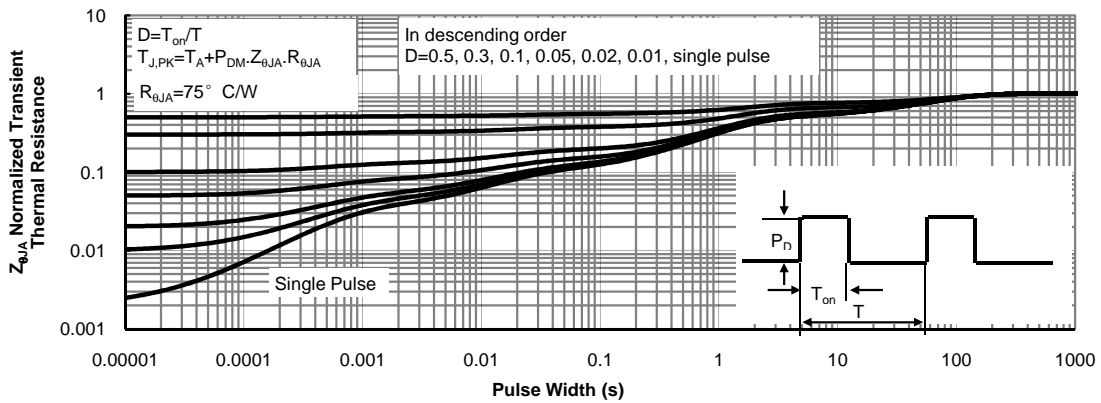
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**

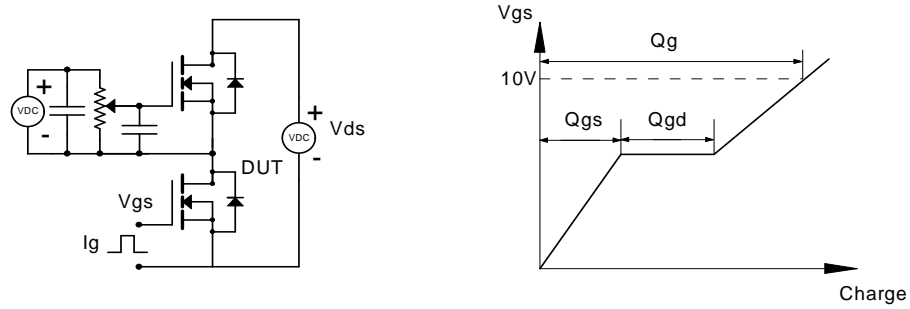


**Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)**

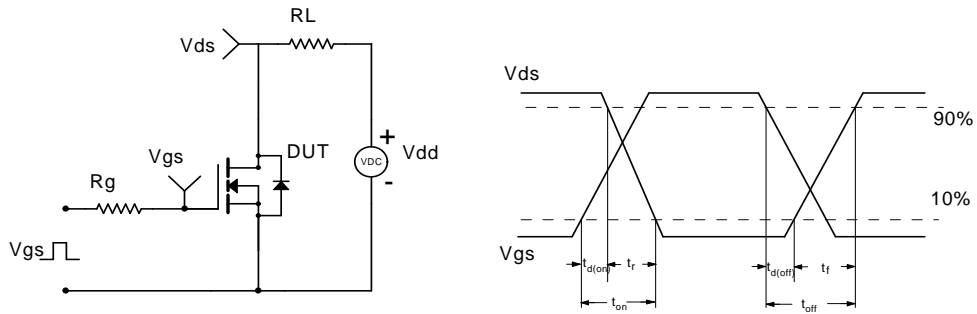


**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

Gate Charge Test Circuit & Waveform



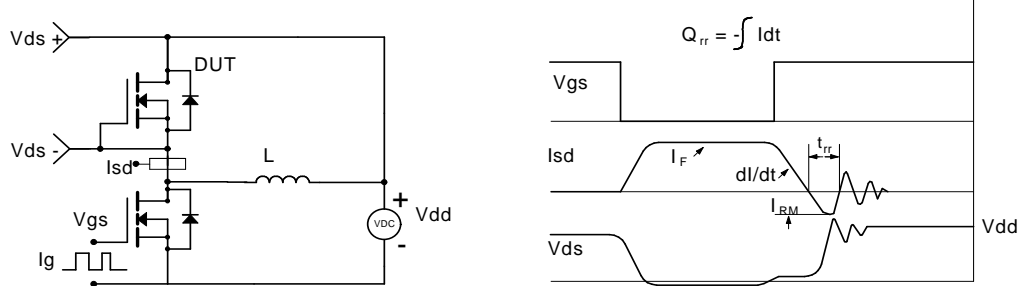
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



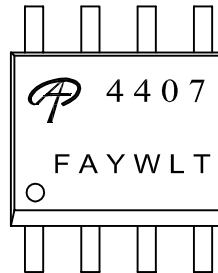
Diode Recovery Test Circuit & Waveforms





|              |                            |
|--------------|----------------------------|
| Document No. | PD-00013                   |
| Version      | F                          |
| Title        | AO4407 Marking Description |

SO-8 PACKAGE MARKING DESCRIPTION



Green product

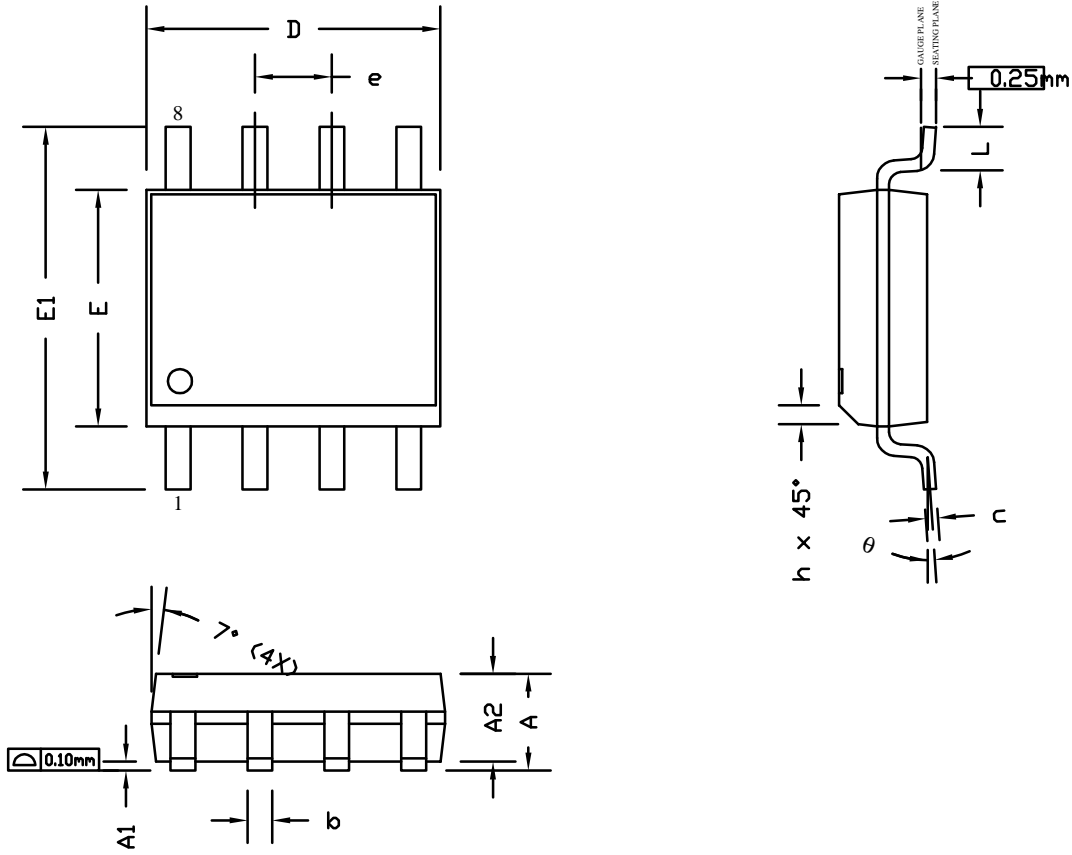
|       |                          |
|-------|--------------------------|
| NOTE: |                          |
| LOGO  | - AOS Logo               |
| 4407  | - Part number code       |
| F     | - Fab code               |
| A     | - Assembly location code |
| Y     | - Year code              |
| W     | - Week code              |
| L&T   | - Assembly lot code      |

| PART NO. | DESCRIPTION   | CODE |
|----------|---------------|------|
| AO4407   | Green product | 4407 |
| AO4407L  | Green product | 4407 |

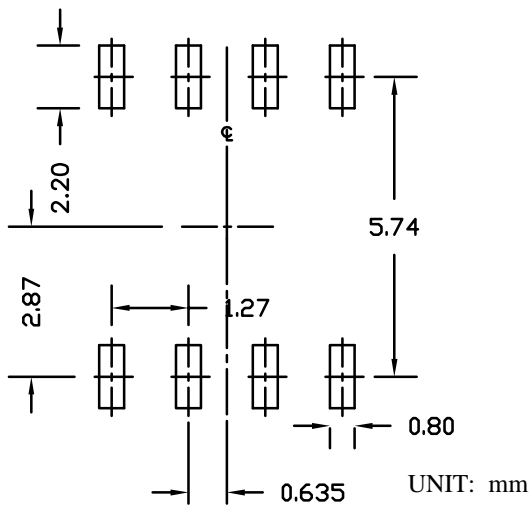


|              |          |
|--------------|----------|
| Document No. | PO-00004 |
| Version      | I        |

S08 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



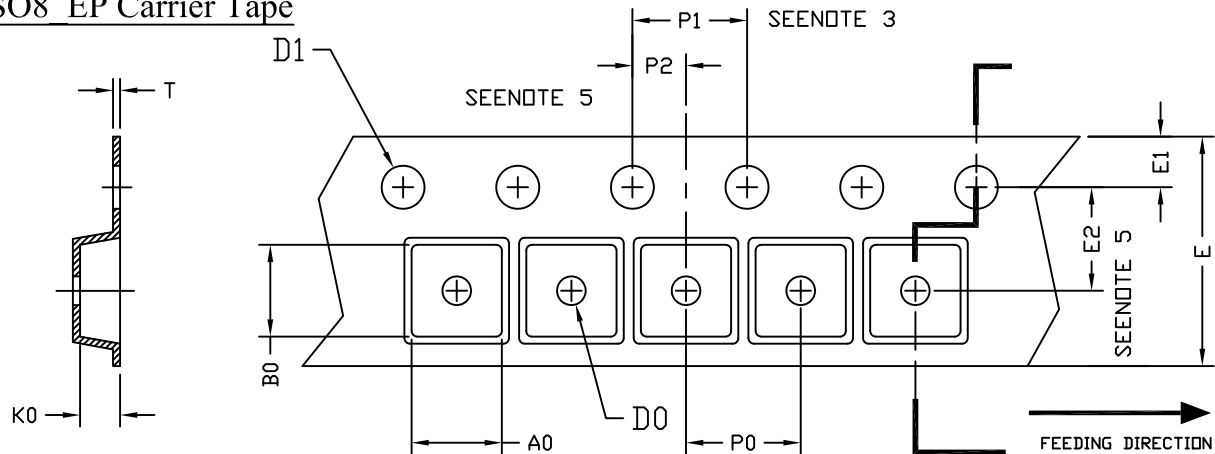
| SYMBOLS | DIMENSIONS IN MILLIMETERS |      |      | DIMENSIONS IN INCHES |       |       |
|---------|---------------------------|------|------|----------------------|-------|-------|
|         | MIN                       | NOM  | MAX  | MIN                  | NOM   | MAX   |
| A       | 1.35                      | 1.65 | 1.75 | 0.053                | 0.065 | 0.069 |
| A1      | 0.10                      | 0.15 | 0.25 | 0.004                | 0.006 | 0.010 |
| A2      | 1.25                      | 1.50 | 1.65 | 0.049                | 0.059 | 0.065 |
| b       | 0.31                      | 0.41 | 0.51 | 0.012                | 0.016 | 0.020 |
| c       | 0.17                      | 0.20 | 0.25 | 0.007                | 0.008 | 0.010 |
| D       | 4.80                      | 4.90 | 5.00 | 0.189                | 0.193 | 0.197 |
| E       | 3.80                      | 3.90 | 4.00 | 0.150                | 0.154 | 0.157 |
| e       | 1.27 BSC                  |      |      | 0.050 BSC            |       |       |
| E1      | 5.80                      | 6.00 | 6.20 | 0.228                | 0.236 | 0.244 |
| h       | 0.25                      | 0.30 | 0.50 | 0.010                | 0.012 | 0.020 |
| L       | 0.40                      | 0.69 | 1.27 | 0.016                | 0.027 | 0.050 |
| θ       | 0°                        | 4°   | 8°   | 0°                   | 4°    | 8°    |

NOTE

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONS ARE INCLUSIVE OF PLATING.
3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
4. DIMENSION L IS MEASURED IN GAUGE PLANE.
5. CONTROLLING DIMENSION IS MILLIMETER.  
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



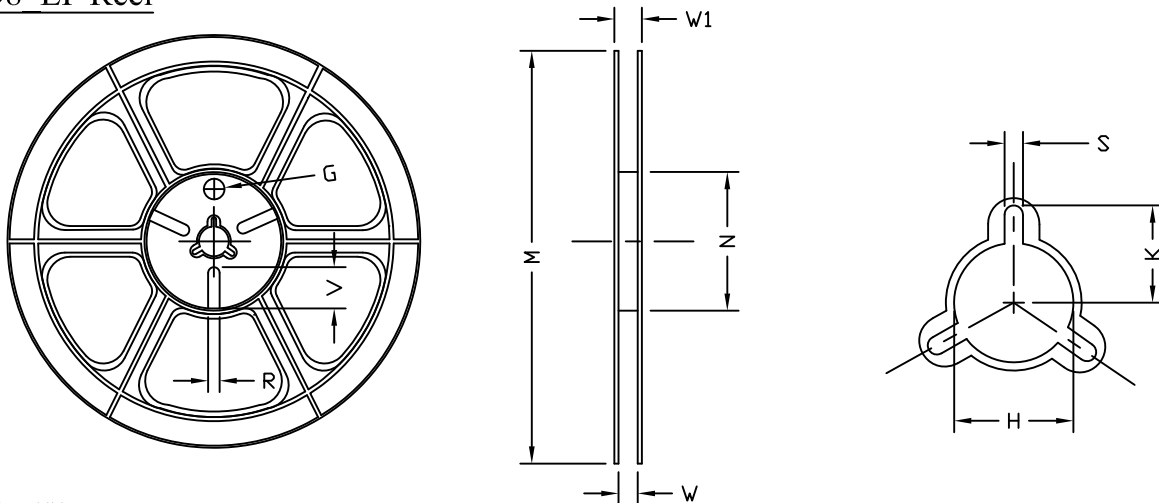
SO8/SO8 EP Carrier Tape



UNIT: MM

| PACKAGE         | A0            | B0            | K0            | D0            | D1            | E              | E1            | E2            | P0            | P1            | P2            | T             |
|-----------------|---------------|---------------|---------------|---------------|---------------|----------------|---------------|---------------|---------------|---------------|---------------|---------------|
| SO-8<br>(12 mm) | 6.40<br>±0.10 | 5.20<br>±0.10 | 2.10<br>±0.10 | 1.60<br>±0.10 | 1.50<br>+0.10 | 12.00<br>±0.30 | 1.75<br>±0.10 | 5.50<br>±0.05 | 8.00<br>±0.10 | 4.00<br>±0.10 | 2.00<br>±0.05 | 0.25<br>±0.05 |

SO8/SO8 EP Reel



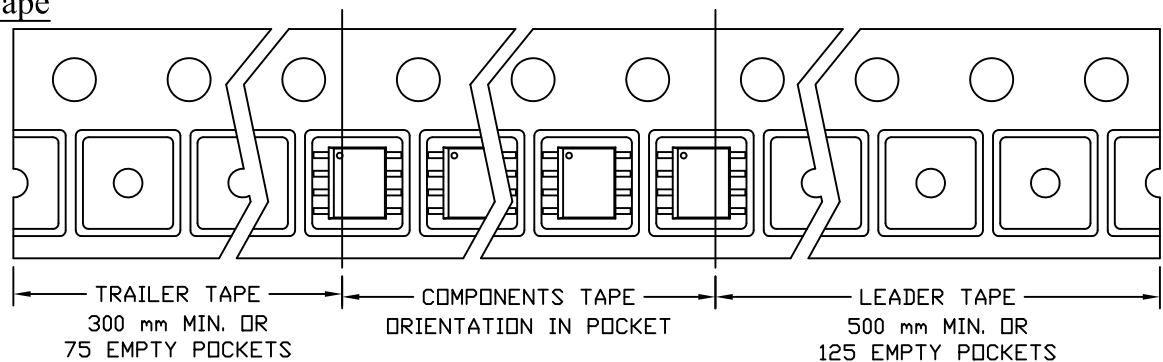
UNIT: MM

| TAPE SIZE | REEL SIZE | M                | N               | W              | W1             | H                        | K     | S             | G   | R   | V   |
|-----------|-----------|------------------|-----------------|----------------|----------------|--------------------------|-------|---------------|-----|-----|-----|
| 12 mm     | ø330      | ø330.00<br>±0.50 | ø97.00<br>±0.10 | 13.00<br>±0.30 | 17.40<br>±1.00 | ø13.00<br>+0.50<br>-0.20 | 10.60 | 2.00<br>±0.50 | --- | --- | --- |

SO8/SO8 EP Tape

Leader / Trailer  
& Orientation

Unit Per Reel:  
3000pcs







# ***AOS Semiconductor Product Reliability Report***

**AO4407 / AO4407L, rev D**

**Plastic Encapsulated Device**

**ALPHA & OMEGA Semiconductor, Inc**

**495 Mercury Drive  
Sunnyvale, CA 94085  
U.S.**

**Tel: (408) 830-9742**

**[www.aosmd.com](http://www.aosmd.com)**

**Dec 27, 2005**

This AOS product reliability report summarizes the qualification result for AO4407. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4407 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

## Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation
- V. Quality Assurance Information

### I. Product Description:

The AO4407 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications. Standard Product AO4407 is Pb-free (meets ROHS & Sony 259 specifications). AO4407L is a Green Product ordering option. AO4407 and AO4407L are electrically identical.

| Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted |                        |                |            |                  |
|--|------------------------|----------------|------------|------------------|
| Parameter  |                        | Symbol         | Maximum    | Units            |
| Drain-Source Voltage   |                        | $V_{DS}$       | -30        | V                |
| Gate-Source Voltage  |                        | $V_{GS}$       | $\pm 25$   | V                |
| Continuous Drain Current   | $T_A=25^\circ\text{C}$ | $I_D$          | -12        | A                |
|  | $T_A=70^\circ\text{C}$ |                | -10        |                  |
| Pulsed Drain Current   |                        | $I_{DM}$       | -60        |                  |
| Power Dissipation  | $T_A=25^\circ\text{C}$ | $P_D$          | 3          | W                |
|  | $T_A=70^\circ\text{C}$ |                | 2.1        |                  |
| Junction and Storage Temperature Range                                 |                        | $T_J, T_{STG}$ | -55 to 150 | $^\circ\text{C}$ |

| Thermal Characteristics     |                     |                 |     |     |                    |
|-----------------------------|---------------------|-----------------|-----|-----|--------------------|
| Parameter                   |                     | Symbol          | Typ | Max | Units              |
| Maximum Junction-to-Ambient | $T \leq 10\text{s}$ | $R_{\theta JA}$ | 28  | 40  | $^\circ\text{C/W}$ |
|                             | Steady-State        |                 | 54  | 75  | $^\circ\text{C/W}$ |
| Maximum Junction-to-Lead    | Steady-State        | $R_{\theta JL}$ | 21  | 30  | $^\circ\text{C/W}$ |

## II. Die / Package Information:

|                                   | <b>AO4407</b>                                     | <b>AO4407L (Green Compound)</b>                   |
|-----------------------------------|---|---|
| <b>Process</b>                    | Standard sub-micron low voltage P channel process | Standard sub-micron low voltage P channel process |
| <b>Package Type</b>               | 8 leads SOIC                                      | 8 leads SOIC                                      |
| <b>Lead Frame</b>                 | Ag with Solder Plate                              | Ag with Solder Plate                              |
| <b>Die Attach</b>                 | Silver-filled Epoxy                               | Silver-filled Epoxy                               |
| <b>Bond wire</b>                  | 2 mils Au wire                                    | 2 mils Au wire                                    |
| <b>Mold Material</b>              | Epoxy resin with silica filler                    | Epoxy resin with silica filler                    |
| <b>Filler % (Spherical/Flake)</b> | 90/10   | 100/0   |
| <b>Flammability Rating</b>        | UL-94 V-0   | UL-94 V-0   |
| <b>Backside Metallization</b>     | Ti / Ni / Ag                                      | Ti / Ni / Ag                                      |
| <b>Moisture Level</b>             | Up to Level 1 *                                   | Up to Level 1 *                                   |

Note \* based on info provided by assembler and mold compound supplier

## III. Result of Reliability Stress for AO4407 (Standard) & AO4407L (Green)

| Test Item                  | Test Condition   | Time Point                | Lot Attribution                                      | Total Sample size          | Number of Failures |
|----------------------------|--|---------------------------|--|----------------------------|--------------------|
| Solder Reflow Precondition | Standard: 1hrPCT+3 cycle reflow@260°C<br>Green: 168hr 85°C /85%RH +3 cycle reflow @260°C | 0hr                       | Standard: 6 lots<br>Green: 16 lots                   | 3300 pcs                   | 0                  |
| HTGB                       | Temp = 150°C, Vgs=100% of Vgsmax   | 168 / 500 hrs<br>1000 hrs | 6 lots<br><br>(Note A*)                              | 492 pcs<br>77+5 pcs / lot  | 0                  |
| HTRB                       | Temp = 150°C, Vds=80% of Vdsmax  | 168 / 500 hrs<br>1000 hrs | 6 lots<br><br>(Note A*)                              | 492 pcs<br>77+5 pcs / lot  | 0                  |
| HAST                       | 130 +/- 2°C, 85%RH, 33.3 psi, Vgs = 80% of Vgs max                                       | 100 hrs                   | Standard: 6 lots<br>Green: 13 lots<br><br>(Note B**) | 1045 pcs<br>50+5 pcs / lot | 0                  |
| Pressure Pot               | 121°C, 15+/-1 PSIG, RH=100%  | 96 hrs                    | Standard: 5 lots<br>Green: 16 lots<br>(Note B**)     | 1155 pcs<br>50+5 pcs / lot | 0                  |
| Temperature Cycle          | -65°C to 150°C, air to air, 0.5hr per cycle  | 250 / 500 cycles          | Standard: 5 lots<br>Green: 15 lots<br><br>(Note B**) | 1100 pcs<br>50+5 pcs / lot | 0                  |

### III. Result of Reliability Stress for AO4407 (Standard) & AO4407L (Green) Continues

|                       |  |                                |                         |   |          |
|-----------------------|--|--------------------------------|-------------------------|---|----------|
| <b>DPA</b>            | <b>Internal Vision<br/>Cross-section<br/>X-ray</b> | <b>NA</b>                      | <b>5<br/>5<br/>5</b>    | <b>5<br/>5<br/>5</b>                      | <b>0</b> |
| <b>CSAM</b>           |  | <b>NA</b>                      | <b>5</b>                | <b>5</b>                                  | <b>0</b> |
| <b>Bond Integrity</b> | <b>Room Temp<br/>150°C bake<br/>150°C bake</b>     | <b>0hr<br/>250hr<br/>500hr</b> | <b>40<br/>40<br/>40</b> | <b>40 wires<br/>40 wires<br/>40 wires</b> | <b>0</b> |
| <b>Solderability</b>  | <b>230°C</b>                                       | <b>5 sec</b>                   | <b>15</b>               | <b>15 leads</b>                           | <b>0</b> |
| <b>Die Shear</b>      | <b>150°C</b>                                       | <b>0hr</b>                     | <b>10</b>               | <b>10</b>                                 | <b>0</b> |

**Note A:** The HTGB and HTRB reliability data presents total of available AO4407 and AO4407L burn-in data up to the published date.

**Note B:** The pressure pot, temperature cycle and HAST reliability data for AO4407 and AO4407L comes from the AOS generic package qualification data.

### IV. Reliability Evaluation

**FIT rate (per billion): 7**

**MTTF =16307 years**

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO3401). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)]$$

$$= 1.83 \times 10^9 / [2 (3 \times 164) (168) (258) + 2 (164) (500)(258) + 2 (2 \times 164) (1000) (258)]$$

$$= 7$$

$$\text{MTTF} = 10^9 / \text{FIT} = 1.42 \times 10^8 \text{hrs} = 16307 \text{ years}$$

**Chi<sup>2</sup>** = Chi Squared Distribution, determined by the number of failures and confidence interval

**N** = Total Number of units from HTRB and HTGB tests

**H** = Duration of HTRB/HTGB testing

**Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [**Af**] =  $\text{Exp} [E_a / k (1/T_j u - 1/T_j s)]$

**Acceleration Factor ratio list:**

|           | <b>55 deg C</b> | <b>70 deg C</b> | <b>85 deg C</b> | <b>100 deg C</b> | <b>115 deg C</b> | <b>130 deg C</b> | <b>150 deg C</b> |
|-----------|-----------------|-----------------|-----------------|------------------|------------------|------------------|------------------|
| <b>Af</b> | <b>258</b>      | <b>87</b>       | <b>32</b>       | <b>13</b>        | <b>5.64</b>      | <b>2.59</b>      | <b>1</b>         |

**Tj s** = Stressed junction temperature in degree (Kelvin), K = C+273.16

**Tj u** = The use junction temperature in degree (Kelvin), K = C+273.16

**k** = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>e V / K



## V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual.

Guaranteed Outgoing Defect Rate: **< 25 ppm**

Quality Sample Plan: conform to **Mil-Std-105D**